

Silicon NPN Power Transistors

2SC2965

DESCRIPTION

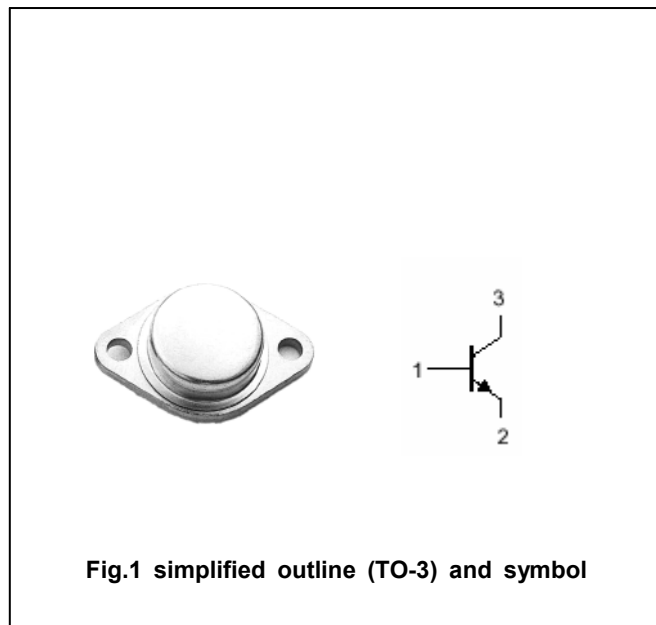
- With TO-3 package
- High breakdown voltage
- Fast switching speed.
- Wide area of safe operation

APPLICATIONS

- For switching regulator applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	150	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon NPN Power Transistors

2SC2965

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA ; R_{BE}=\infty$	450			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	600			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=10A ; I_B=2A$			1.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=10A ; I_B=2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V ; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=10A ; V_{CE}=5V$	7		20	
f_T	Transition frequency	$I_C=2A ; V_{CE}=10V$		28		MHz
C_{OB}	Collector output capacitance	$I_E=0 ; V_{CB}=10V, f=1MHz$		230		pF

Silicon NPN Power Transistors

2SC2965

PACKAGE OUTLINE

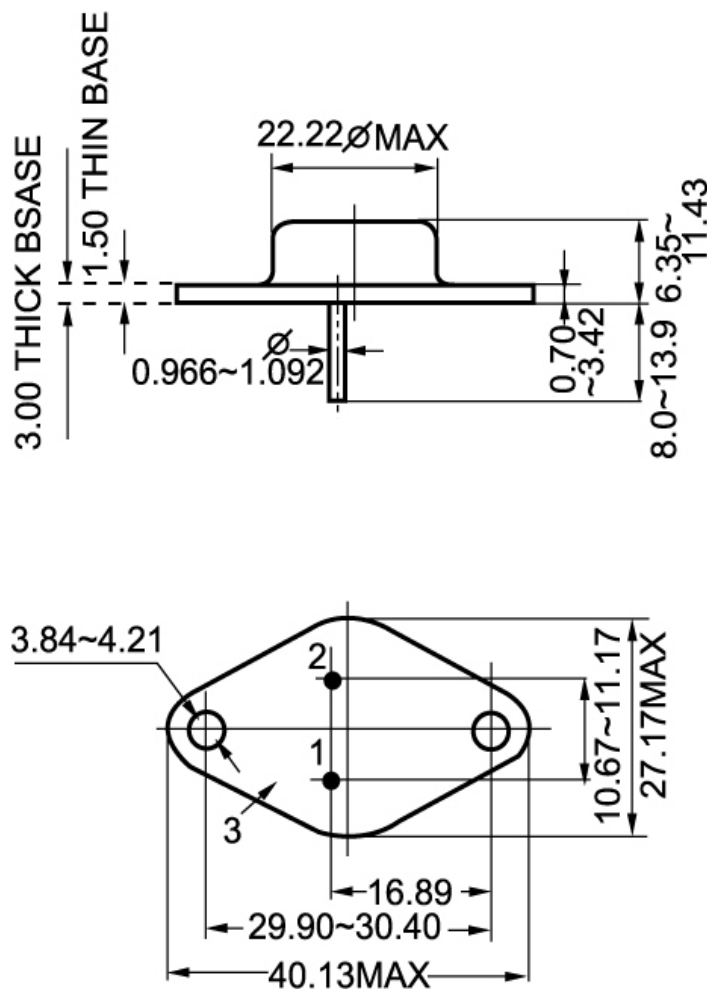


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)